

**IRF610-613
MTP2N18/2N20
N-Channel Power MOSFETs,
3.5 A, 150-200 V**

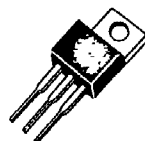
Power And Discrete Division

Description

These devices are n-channel, enhancement mode, power MOSFETs designed especially for high speed applications, such as switching power supplies, converters, AC and DC motor controls, relay and solenoid drivers and other pulse circuits.

- Low $R_{DS(on)}$
- V_{GS} Rated at ± 20 V
- Silicon Gate for Fast Switching Speeds
- I_{DSS} , $V_{DS(on)}$ Specified at Elevated Temperature
- Rugged
- Low Drive Requirements
- Ease of Paralleling

TO-220AB



IRF610
IRF611
IRF612
IRF613
MTP2N18
MTP2N20

Maximum Ratings

Symbol	Characteristic	Rating IRF610/612 MTP2N20	Rating MTP2N18	Rating IRF611/613	Unit
V_{DSS}	Drain to Source Voltage ¹	200	180	150	V
V_{DGR}	Drain to Gate Voltage ¹ $R_{GS} = 20 \text{ k}\Omega$	200	180	150	V
V_{GS}	Gate to Source Voltage	± 20	± 20	± 20	V
T_J , T_{slg}	Operating Junction and Storage Temperatures	-55 to +150	-55 to +150	-55 to +150	$^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" From Case for 5 s	275	275	275	$^{\circ}\text{C}$

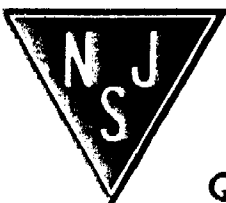
Maximum On-State Characteristics

		IRF610/611	MTP2N18/20	IRF612/613	
$R_{DS(on)}$	Static Drain-to-Source On Resistance	1.5	1.8	2.4	Ω
I_D	Drain Current				A
	Continuous at $T_C = 25^{\circ}\text{C}$	2.5	3.25	2.0	
	Continuous at $T_C = 100^{\circ}\text{C}$	1.5	2.25	1.25	
	Pulsed	10	9.0	8.0	

Maximum Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.4	2.5	6.4	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	80	80	80	$^{\circ}\text{C/W}$
P_D	Total Power Dissipation at $T_C = 25^{\circ}\text{C}$	20	50	20	W

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Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
V _{(BR)DSS}	Drain Source Breakdown Voltage ¹			V	V _{GS} = 0 V, I _D = 250 μA
	IRF610/612/MTP2N20	200			
	MTP2N18	180			
	IRF611/613	150			
I _{DSS}	Zero Gate Voltage Drain Current		250	μA	V _{DS} = Rated V _{DSS} , V _{GS} = 0 V
			1000	μA	V _{DS} = 0.8 x Rated V _{DSS} , V _{GS} = 0 V, T _C = 125°C
I _{GSS}	Gate-Body Leakage Current		± 500	nA	V _{GS} = ± 20 V, V _{DS} = 0 V
On Characteristics					
V _{GS(th)}	Gate Threshold Voltage			V	I _D = 250 μA, V _{DS} = V _{GS} I _D = 1 mA, V _{DS} = V _{GS}
	IRF610-613	2.0	4.0		
	MTP2N18/20	2.0	4.5		
R _{DS(on)}	Static Drain-Source On-Resistance ²			Ω	V _{GS} = 10 V, I _D = 1.25 A
	IRF610/611		1.5		I _D = 1.0 A
	IRF612/613		2.4		
	MTP2N18/20		1.8		
V _{DS(on)}	Drain-Source On-Voltage ²		4.4	V	V _{GS} = 10 V; I _D = 2.0 A
	MTP2N18/2N20		3.6	V	V _{GS} = 10 V; I _D = 1.0 A; T _C = 100°C
g _{fs}	Forward Transconductance	0.8		S (τ)	V _{DS} = 10 V, I _D = 1.25 A
Dynamic Characteristics					
C _{iss}	Input Capacitance		200	pF	V _{DS} = 25 V, V _{GS} = 0 V f = 1.0 MHz
C _{oss}	Output Capacitance		80	pF	
C _{rss}	Reverse Transfer Capacitance		25	pF	
Switching Characteristics (T _C = 25°C, Figures 11, 12) ³					
t _{d(on)}	Turn-On Delay Time		15	ns	V _{DD} = 50 V, I _D = 1.25 A V _{GS} = 10 V, R _{GEN} = 50 Ω R _{GS} = 50 Ω
t _r	Rise Time		25	ns	
t _{d(off)}	Turn-Off Delay Time		15	ns	
t _f	Fall Time		15	ns	
Q _g	Total Gate Charge		7.5	nC	V _{GS} = 10 V, I _D = 3.0 A V _{DD} = 45 V

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Electrical Characteristics (Cont.) ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Typ	Max	Unit	Test Conditions
V_{SD}	Diode Forward Voltage IRF610/611		2.0	V	$I_S = 2.5 \text{ A}; V_{GS} = 0 \text{ V}$
	IRF612/613		1.8	V	$I_S = 2.0 \text{ A}; V_{GS} = 0 \text{ V}$
t_{rr}	Reverse Recovery Time	290		ns	$I_S = 2.5 \text{ A}; dI_S/dt = 25 \text{ A}/\mu\text{S}$

Notes

- $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$
- Pulse test: Pulse width $\leq 80 \mu\text{s}$, Duty cycle $\leq 1\%$
- Switching time measurements performed on LEM TR-50 test equipment.

Typical Performance Curves

Figure 1 Output Characteristics

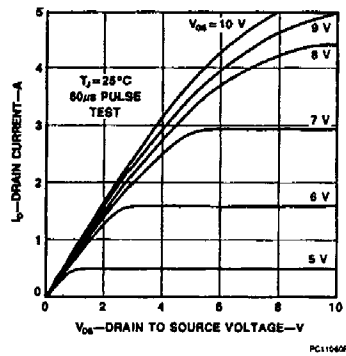


Figure 2 Static Drain to Source Resistance vs Drain Current

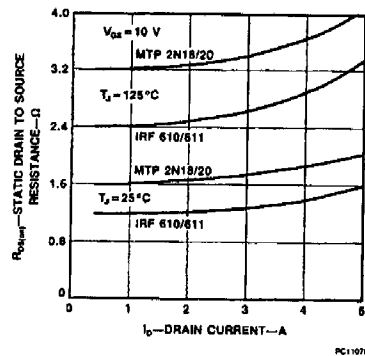


Figure 3 Transfer Characteristics

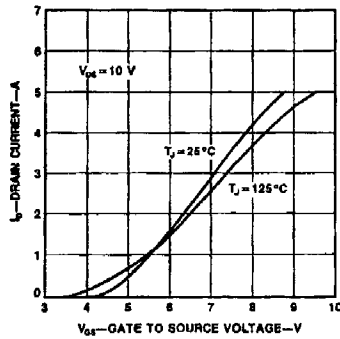


Figure 4 Temperature Variation of Gate to Source Threshold Voltage

